

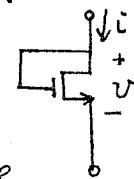
淡江大學八十七學年度日間部轉學生入學考試試題

系別：電機工程學系三年級

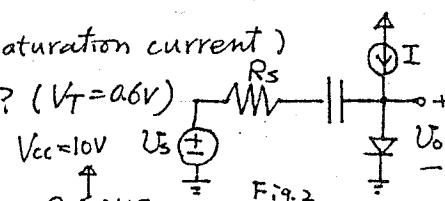
科目：電子學

本試題共 1 頁

1. For the diode-connected enhancement MOSFET of Fig. 1, find an expression for its (20%) incremental resistance r at $V = 2V_T$. Neglect the small effect of r_0 . Evaluate r for the case $V_T = 1V$, $\mu_n C_{ox} = 20\mu A/V^2$, $W = 6\mu m$ and $L = 30\mu m$.



2. In the circuit shown in Fig. 2, I is a dc current and V_S is a sinusoidal signal. (20%) (1) Use the diode small signal model to show that the Signal component of the output signal voltage $V_O = ?$ (in terms of V_T , R_S , I , V_S) assuming $i-v$ of diode is $i \approx I_s e^{V/V_T}$. (I_s : saturation current) (2) If $V_S = 10mV$, $I = 1mA$, $R_S = 1k\Omega$, Find $V_O = ?$ ($V_T = 0.6V$)



3. Determine the voltage gain of Fig. 3, $\frac{V_O}{V_i} = ?$ (20%) (V_O, V_i are small signal.)

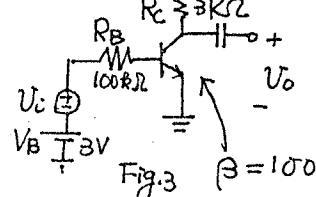


Fig. 2

Fig. 3

4. Determine the circuit shown in Fig. 4, $V_{GS} = ?$, $I_D = ?$ (20%)

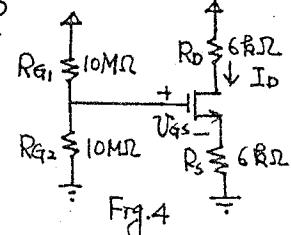


Fig. 4

5. Consider the current mirror circuit of Fig. 5, with $V_{SS} = -5V$, $I_{REF} = 10\mu A$, (20%) $V_T = 1V$, $\mu_n C_{ox} = 20\mu A/V^2$, $V_A = 20V$, $L = 10\mu m$, $W = 40\mu m$ for Q_1, Q_2, Q_3, Q_4 . Find (1) the output resistance (2) the lowest allowable output voltage.

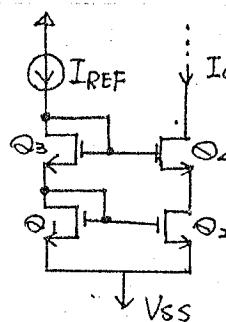


Fig. 5